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Attorney's Docket No.: 07977-093002 / US3164D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hisashi Ohtani, et al. Art Unit : 2815
Serial No.: 09/379,702 Examiner : Eugene Lee
Filed : August 24, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the action mailed February 14, 2002, please
amend the application as follows:

In the claims:

Please cancel all pending claims, specifically claims
2-12, 14-25, 27, 28, and 30-44.

Please substitute new claims 45-64 as follows:

*sub G1
E,*

--45. A semiconductor device comprising:
a crystalline semiconductor island comprising silicon
over
a substrate, the crystalline semiconductor island
comprising a source region, a drain region and a channel
formation region provided between the source and the drain
region; and

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I hereby certify under 37 CFR §1.8(a) that this
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